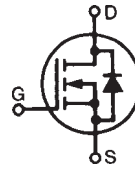


# HiPerFET™ Power MOSFET Q2-Class

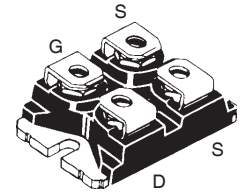
## IXFN70N60Q2

$V_{DSS} = 600V$   
 $I_{D25} = 70A$   
 $R_{DS(on)} \leq 88m\Omega$   
 $t_{rr} \leq 250ns$



N-Channel Enhancement Mode  
 Avalanche Rated, Low  $Q_g$ , Low Intrinsic  $R_g$   
 High  $dV/dt$ , Low  $t_{rr}$

miniBLOC, SOT-227 B  
 E153432



G = Gate                      D = Drain  
 S = Source

Either Source terminal at miniBLOC can be used as Main or Kelvin Source

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $150^\circ C$	600	V
$V_{DGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$	600	V
$V_{GSS}$	Continuous	$\pm 30$	V
$V_{GSM}$	Transient	$\pm 40$	V
$I_{D25}$	$T_C = 25^\circ C$	70	A
$I_{DM}$	$T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$	280	A
$I_A$	$T_C = 25^\circ C$	70	A
$E_{AS}$	$T_C = 25^\circ C$	5	J
$dV/dt$	$I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ C$	20	V/ns
$P_D$	$T_C = 25^\circ C$	890	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$T_L$	1.6mm (0.062 in.) from Case for 10s	300	$^\circ C$
$V_{ISOL}$	50/60Hz, RMS $t = 1min$	2500	V~
	$I_{ISOL} \leq 1mA$ $t = 1s$	3000	V~
$M_d$	Mounting Torque	1.5/13	Nm/lb.in.
	Terminal Connection Torque	1.3/11.5	Nm/lb.in.
<b>Weight</b>		30	g

### Features

- Double Metal Process for Low Gate Resistance
- miniBLOC, with Aluminium Nitride Isolation
- Avalanche Rated
- Low Package Inductance
- Fast Intrinsic Rectifier

### Applications

- DC-DC Converters
- Switched-Mode and Resonant-Mode Power Supplies
- DC Choppers
- Pulse Generators

### Advantages

- Easy to Mount
- Space Savings
- High Power Density

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 1mA$	600		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 8mA$	3.0		5.5 V
$I_{GSS}$	$V_{GS} = \pm 30V$ , $V_{DS} = 0V$			$\pm 200$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$			50 $\mu A$
	$T_J = 125^\circ C$			3 mA
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1			88 m $\Omega$

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 10\text{V}$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1	36	50	S
$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$		12	nF
$C_{oss}$			1340	pF
$C_{rss}$			345	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 35\text{A}$ $R_G = 1\Omega$ (External)		26	ns
$t_r$			25	ns
$t_{d(off)}$			60	ns
$t_f$			12	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$		265	nC
$Q_{gs}$			57	nC
$Q_{gd}$			120	nC
$R_{thJC}$			0.14	$^\circ\text{C/W}$
$R_{thCS}$		0.05		$^\circ\text{C/W}$

### Source-Drain Diode

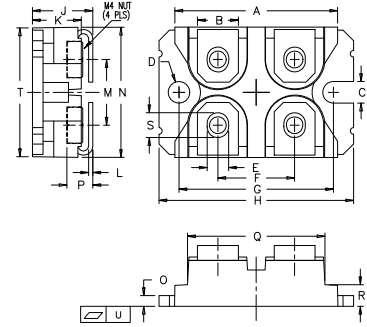
Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			70 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			280 A
$V_{SD}$	$I_F = I_S$ , $V_{GS} = 0\text{V}$ , Note 1			1.5 V
$t_{rr}$	$I_F = 25\text{A}$ , $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$ , $V_{GS} = 0\text{V}$			250 ns
$Q_{RM}$			1.2	$\mu\text{C}$
$I_{RM}$			8.0	A

Notes1: Pulse Test,  $t \leq 300\mu\text{s}$ ; Duty Cycle,  $d \leq 2\%$ .

### Ordering Information

The IXFN70N60Q2 is also available with brass capture nuts in place of the normal Zinc coated steel capture nuts. The ordering part number is IXFN70N60Q2-BN.

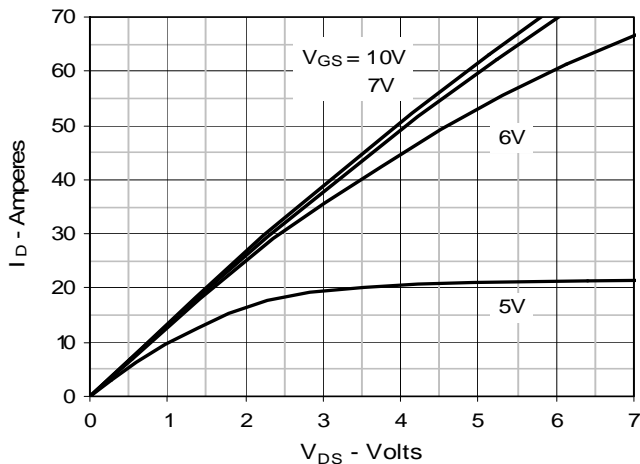
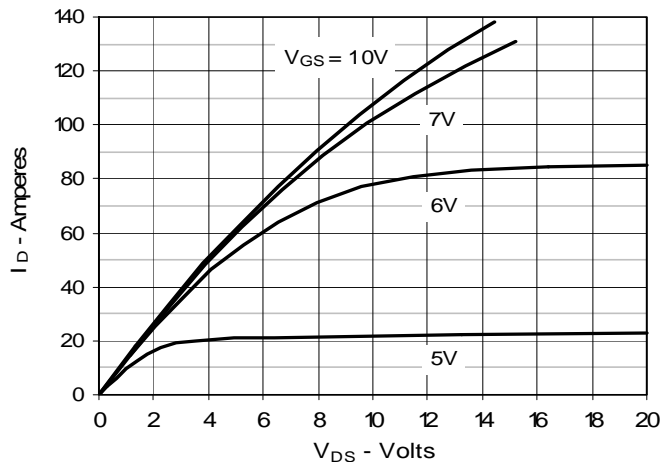
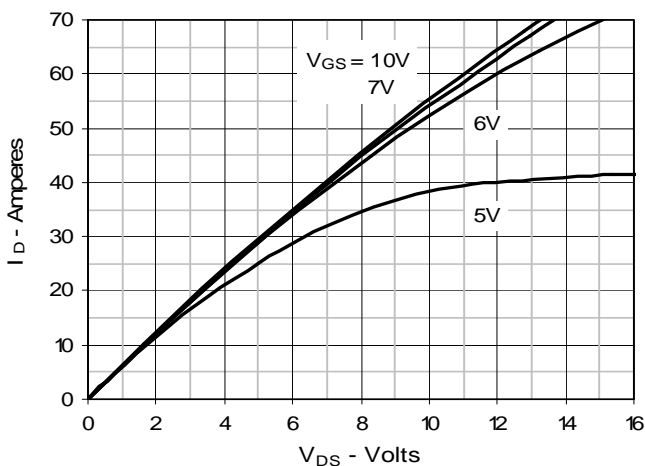
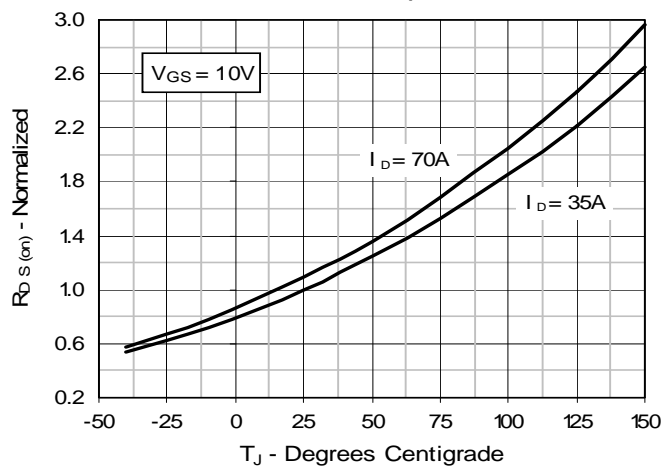
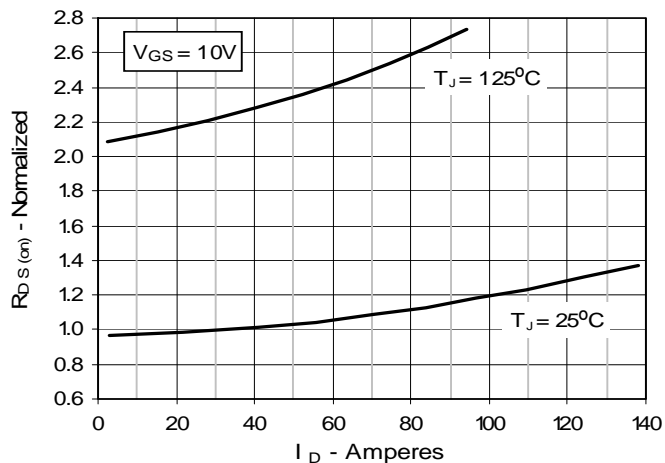
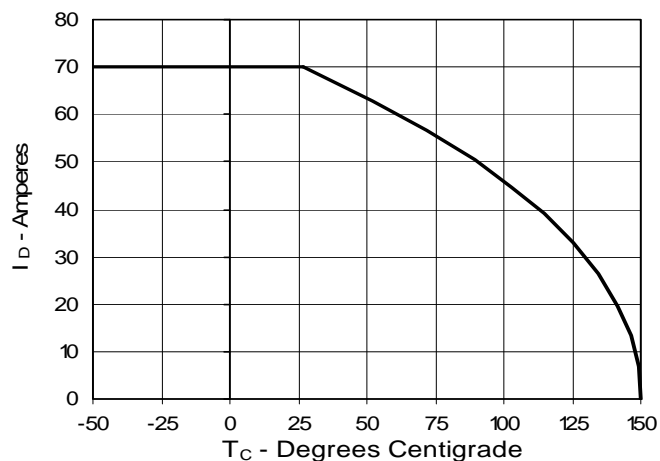
### SOT-227B Outline



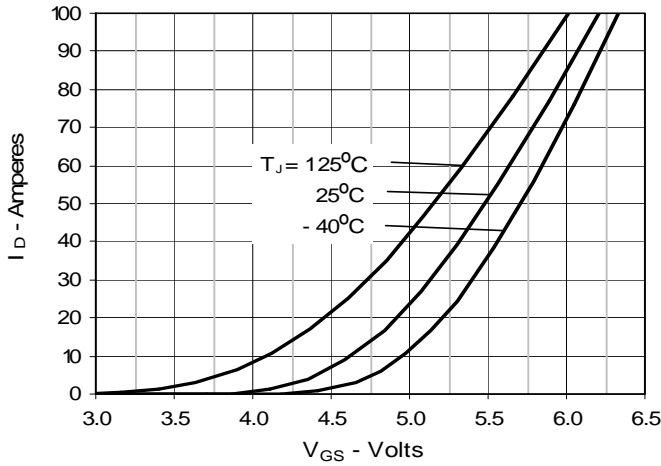
SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

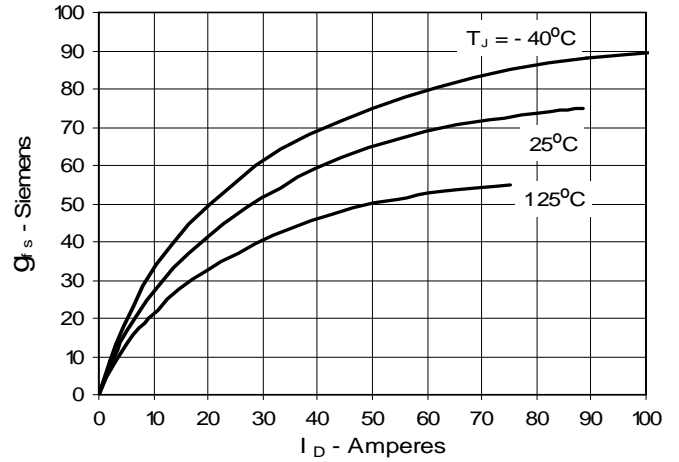
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

**Fig. 1. Output Characteristics**  
 @ 25°C

**Fig. 2. Extended Output Characteristics**  
 @ 25°C

**Fig. 3. Output Characteristics**  
 @ 125°C

**Fig. 4.  $R_{DS(on)}$  Normalized to 0.5  $I_{D25}$  Value vs. Junction Temperature**

**Fig. 5.  $R_{DS(on)}$  Normalized to 0.5  $I_{D25}$  Value vs.  $I_D$** 

**Fig. 6. Drain Current vs. Case Temperature**


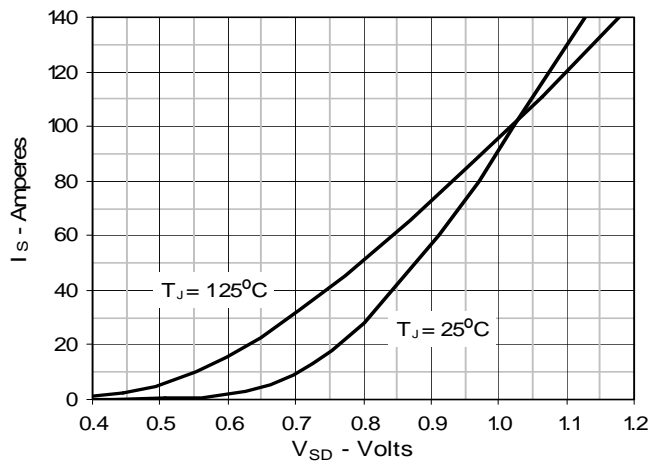
**Fig. 7. Input Admittance**



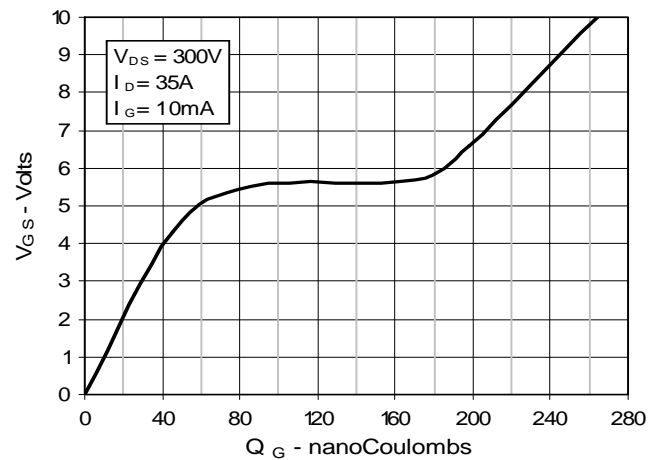
**Fig. 8. Transconductance**



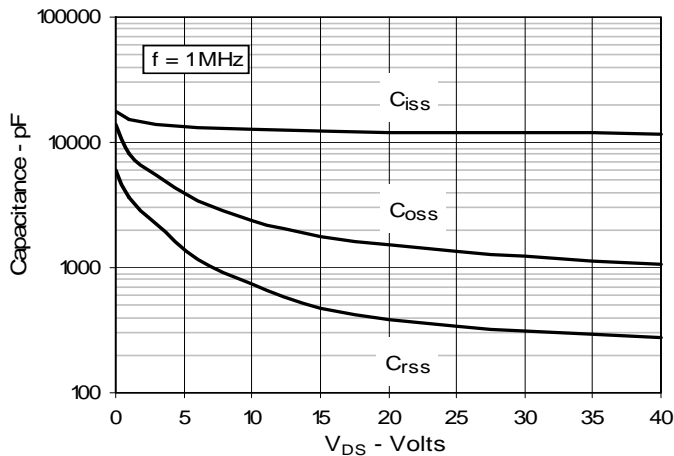
**Fig. 9. Source Current vs. Source-To-Drain Voltage**



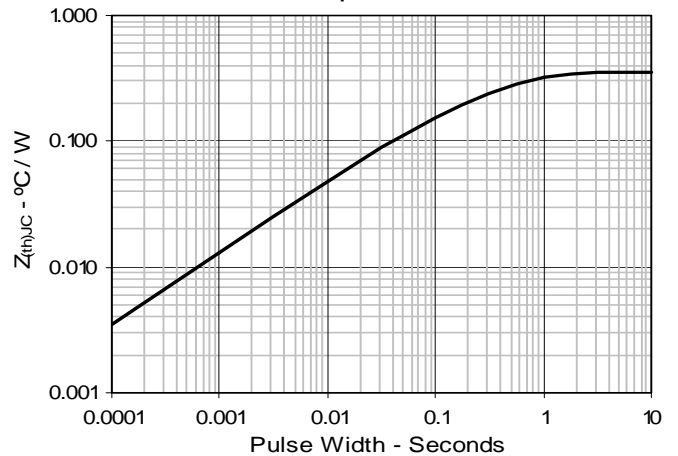
**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Maximum Transient Thermal Impedance**





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